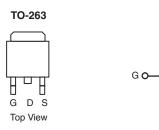


Vishay Siliconix

Automotive N-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0035				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 V$	0.0053				
I _D (A)	120				
Configuration	Single				



FEATURES

- AUTOMOTIVE • Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Package with Low Thermal Resistance
- AEC-Q101 Qualified^d
- 100 % $\rm R_g$ and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

Pro
RoHS
COMPLIANT

HALOGEN FREE

D

ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM120N04-03L-GE3		

ABSOLUTE MAXIMUM RATINGS (T	_C = 25 °C, unles	s otherwise noted	(k		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	± 20	v	
Continuous Drain Current	$T_C = 25 \ ^{\circ}C^a$	- I _D -	120		
	T _C = 125 °C		105		
Continuous Source Current (Diode Conduction) ^a		I _S	120	А	
Pulsed Drain Current ^b		I _{DM}	480		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	54		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	145	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	230	w	
	T _C = 125 °C	P _D	76		
Operating Junction and Storage Temperature Ran	nge	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W	
unction-to-Case (Drain)		R _{thJC}	0.65	C/ W	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static					•			
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0$, $I_D = 250 \ \mu A$		40	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, $V_{GS} = \pm 20$ V	-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	250		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	120	-	-	Α	
		V _{GS} = 10 V	I _D = 30 A	-	0.0027	0.0035	Ω	
Drain-Source On-State Resistance ^a	Р	$V_{GS} = 10 V$	$I_D = 30 \text{ A}, \text{T}_\text{J} = 125 \ ^\circ\text{C}$	-	-	0.0057		
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 30 A, T _J = 175 °C	-	-	0.0070		
		$V_{GS} = 4.5 V$	I _D = 20 A	-	0.0041	0.0053		
Forward Transconductanceb	9 _{fs}	V _{DS}	= 15 V, I _D = 30 A	-	106	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	4252	5315	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$		-	854	1070		
Reverse Transfer Capacitance	C _{rss}	1		-	472	590		
Total Gate Charge ^c	Qg		V _{DS} = 20 V, I _D = 110 A	-	93	140	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V		-	14.6	-		
Gate-Drain Charge ^c	Q _{gd}			-	19.2	-		
Gate Resistance	Rg	f = 1 MHz		0.5	1.1	1.7	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	15	23		
Rise Time ^c	t _r	$\label{eq:VDD} \begin{array}{l} V_{DD} = 20 \; V, \; R_{L} = 0.18 \; \Omega \\ I_{D} \cong 110 \; A, \; V_{GEN} = 10 \; V, \; R_{g} = 1 \; \Omega \end{array}$		-	13	20	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	52	78		
Fall Time ^c	t _f			-	16	24		
Source-Drain Diode Ratings and Char	acteristics ^b				•			
Pulsed Current ^a	I _{SM}			-	-	480	А	
	-31/1							

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

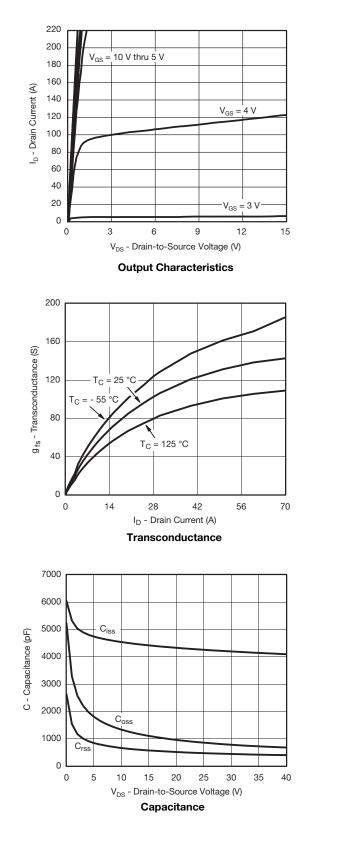
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

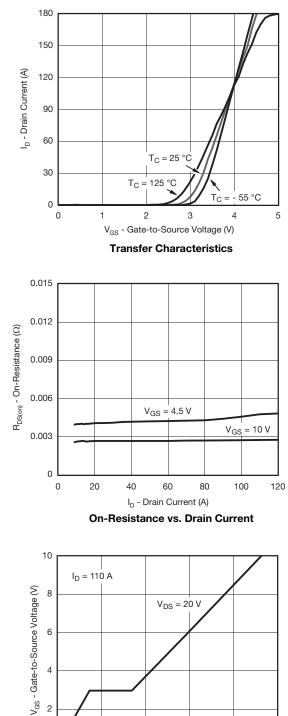
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)





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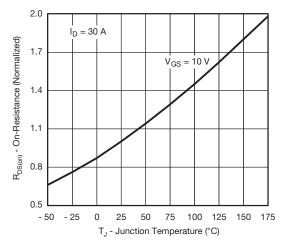
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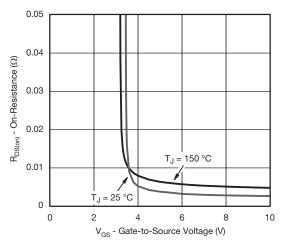


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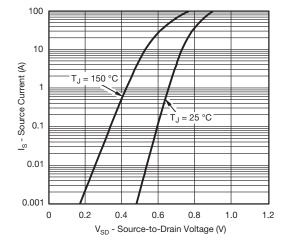
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



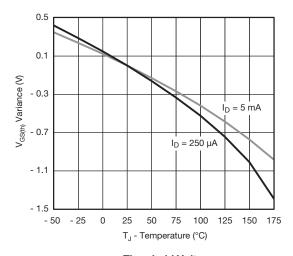




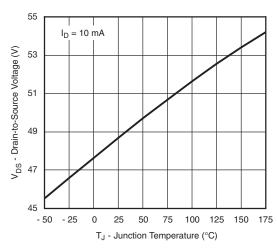
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature

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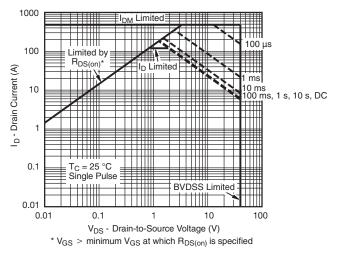
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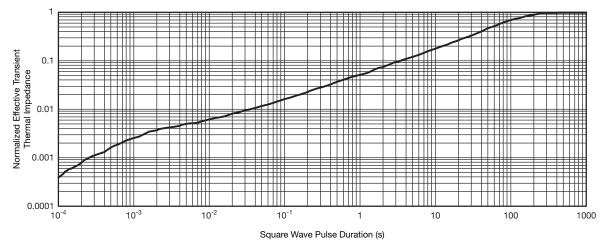


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THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area



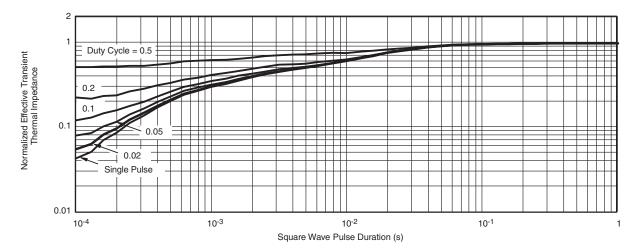
Normalized Thermal Transient Impedance, Junction-to-Ambient





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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

• The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?67061.

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